EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	("3795977" | "5811181").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:02
L2	410660	"metal oxide" or (metal adj oxide) or metal? oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:02
L3	6	(jp-08306806-$ jp-07263646-$ jp-08161933-$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/07 12:02
L4	18	(jp-10341002-$ jp-08031960-$ jp-1052397-$ jp-10152398-$ jp-2003077911-$ jp-2814416-$ jp-2779997-$ jp-09306806-$ jp-07263646-$ jp-08161933-$ JP-50004986-$ jp-49034390).did. ("3795977" "5811181").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/07 12:02
L5	1053	((HIIDEAKI) near2 (SAKAI)).INV. ((MASARU) near2 (SHIMADA)).INV. ((YOSHITO) near2 (JIN)).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/07 12:02
L6	69221	source drain gate 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:05
L7	213331	gate with insulat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:06

L8	30733	6 7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:06
L9	23804	6 7 electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:06
L10	14253	9 (resistance or resistivitiy)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:06
L11	194	bistable 10	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:06
L12	5	(257/1-5 or 438/102-103 or 365/163).ccls. 11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:07
L13	731	ueno.inv. 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:19
L14	129	ueno.inv. 6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:19
L15	99	ueno.inv. 6 7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:19
L16	9824	"srtio.sub.3"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:20

L18	1121	srtio	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:20
L20	120	sr adj ti adj o	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:20
L25	73	ueno.inv. 10	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:22
L26	21	16 11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:23
L27	2	16.ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:24
L28	25	16 with fet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:25
L29	147	16 with (transistor or fet)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:25
L30	294128	gate with (oxide or insulat$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:25
L31	16	28 30	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:25

L32	0	bistable 31	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:28
L33	6	bistable 29	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 12:28
L35	0	2005/0111256.PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 18:00
L36	2	"20050111256".PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 18:00
S2	6	(jp-08306806-$ jp-07263646-$ jp-08161933-$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:27
S3	2	"US 20070107774"	US-PGPUB; USPAT; USOCR; DERWENT	AND	ON	2008/12/17 19:28
S4	18	(jp-10341002-$ jp-08031960-$ jp-1052397-$ jp-10152398-$ jp-2003077911-$ jp-2814416-$ jp-2779997-$ jp-09306806-$ jp-07263646-$ jp-08161933-$ JP-50004986-$ jp-49034390).did. ("3795977" "5811181").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:33
S5	10	((HIDEAKI) near2 (SAKAI)).INV. ((MASARU) near2 (SHIMADA)).INV. ((YOSHITO) near2 (JIN)).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/17 19:33

S6	1042	((HIDEAKI) near2 (SAKAI)).INV. ((MASARU) near2 (SHIMADA)).INV. ((YOSHITO) near2 (JIN)).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:33
S7	388260	"metal oxide" or (metal adj oxide) or metal? oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/17 19:34
S8	58701	electrode resistance oxide S7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/17 19:35
S9	5327	electrode resistance oxide S7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2008/12/17 19:35
S10	170	(electrode resistance oxide S7).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2008/12/17 19:35
S11	1	S10 and S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2008/12/17 19:36
S12	1042	((HIDEAKI) near2 (SAKAI)).INV. ((MASARU) near2 (SHIMADA)).INV. ((YOSHITO) near2 (JIN)).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 12:15
S13	388630	"metal oxide" or (metal adj oxide) or metal? oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:15
S14	171	(electrode resistance oxide S13).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2008/12/18 12:15

S15	1	S14 and S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2008/12/18 12:15
S16	6	(jp-08306806-$ jp-07263646-$ jp-08161933-$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 12:16
S17	18	(jp-10341002-$ jp-08031960-$ jp-1052397-$ jp-10152398-$ jp-2003077911-$ jp-2814416-$ jp-2779997-$ jp-09306806-$ jp-07263646-$ jp-08161933-$ JP-50004986-$ jp-49034390).did. ("3795977" "5811181").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 12:16
S18	0	S16 S17 S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:16
S19	2	(S16 or S17) S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:16
S20	14106	(particles powder) same S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:20
S21	77620	(particles powder) same S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 12:20
S22	58786	electrode resistance oxide S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:21

S23	5332	electrode resistance oxide $13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2008/12/18 12:21
S24	738	S21 S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2008/12/18 12:22
S25	78141	("phase change" or phase?change or (phase adj change))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:23
S26	13	S24 S25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:23
S27	3039	S13 S25 (particles or powder)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:32
S28	201858	electrode resistance oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:32
S29	995	S13 S25 S28 (particles or powder)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:32
S30	448	S21 S29	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:32
S31	356	S21 S29 state	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:32

S32	55230	bi?stable or bistable or (bi adj stable)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:33
S33	40	S31 S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 12:33
S34	89	(bi?stable or bistable or (bi adj stable)) adj resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:03
S35	49	S34 S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:04
S36	20	S34 same S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:04
S37	1833	(bi?stable or bistable or (bi adj stable)) with resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:51
S38	189623	source drain gate electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:51
S39	63	S37 S38 S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:51
S40	61	S37 S38 S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:52

S41	99	S39 or S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:52
S42	25	S39 S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 13:52
S43	130	(bi or bismuth) adj (ti or titanium) adj (oxygen or o)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 14:05
S44	245	"bitio" or ((bi or bismuth) adj (ti or titanium) adj (oxygen or o))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 14:05
S45	2	(bi?stable or bistable or (bi adj stable))S44	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/12/18 14:06
S46	2	"5811818".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 15:26
S47	2	"5811181".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/18 15:26
S48	1053	((HIDEAKI) near2 (SAKAI)).INV. ((MASARU) near2 (SHIMADA)).INV. ((YOSHITO) near2 (JIN)).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 21:01
S49	409962	"metal oxide" or (metal adj oxide) or metal? oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/01 21:01

S50	180	(electrode resistance oxide $49).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:01
S51	1	$50 and $48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:01
S52	25	$50 and (gate adj (oxide or insulator))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:02
S53	20	source drain gate $49 ternary	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:03
S54	0	source drain gate 2binary	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:04
S55	222	source drain gate $49 binary	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:04
S56	5634	$49 electrode resistance oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:04
S57	6	$55 $56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:04
S58	3	source drain gate (binary adj $49)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:06

S59	9	"resistivity switching binary metal oxide"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/01 21:07
S60	7	(resistivity switching binary metal oxide) and source and drain and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/01 21:12
S61	10	(resistivity switching) and (binary metal oxide) and source and drain and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/01 21:14
S62	0	(resistivity switching) and (ternary metal oxide) and source and drain and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/01 21:15
S63	133	(resistivity switching) and (metal oxide) and source and drain and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/01 21:15
S64	2	((resistivity or resistance) switching) and (ternary metal oxide) and source and drain and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/01 21:15

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